Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(ild or interlayer near dielectric) and (integrated near circuit) and (alignment near mark41) and (hardmask or hard near mask) and (tan or tantalum near nitride) and (wavelength) and (resistiv\$3) and (opening or aperture or hole or via) and (pattern\$3 or etch43) and (conductiv43).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:27
L2		(ild or interlayer near dielectric) and (integrated near circuit) and (alignment near mark\$1) and (hardmask or hard near mask) and (tan or tantalum near nitride) and (wavelength) and (resistiv\$3) and (opening or aperture or hole or via) and (pattern\$3 or etch43) and (conductiv43).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2005/10/03 16:28
L3	0	(ild or interlayer near dielectric) and (integrated near circuit) and (alignment near mark\$1) and (hardmask or hard near mask) and (tan or tantalum near nitride) and (wavelength) and (resistiv\$3) and (opening or aperture or hole or via) and (pattern\$3 or etch43) and (conductiv43)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:28
L4	2	(ild or interlayer near dielectric) and (integrated near circuit) and (alignment near mark\$1) and (hardmask or hard near mask) and (tan or tantalum near nitride) and (wavelength) and (resistiv\$3) and (opening or aperture or hole or via) and (pattern\$3 or etch43) and (conductiv\$3).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:28
L5	2	(ild or interlayer near dielectric) and (integrated near circuit) and (alignment near mark\$1) and (hardmask or hard near mask) and (tan or tantalum near nitride) and (wavelength) and (resistiv\$3) and (opening or aperture or hole or via) and (pattern\$3 or etch\$3) and (conductiv\$3).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:28

L6	2	(ild or interlayer near dielectric) and (integrated near circuit) and (alignment near mark\$1) and (hardmask or hard near mask) and (tan or tantalum near nitride) and (wavelength) and (resistiv\$3) and (opening or aperture or hole or via) and (pattern\$3 or etch\$3) and	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:28
		(conductiv\$3)				